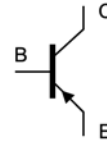


**Features**

- PNP transistors in Jedec TO-18 metal case.
- Designed for high speed switching application.
- Low leakage currents and low saturation voltage.



Schematic Diagram



TO-18

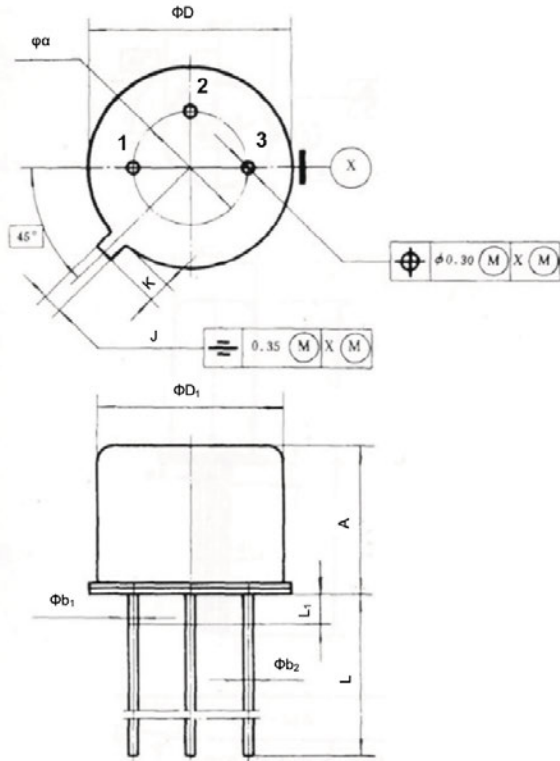
**Absolute Maximum Ratings** ( $T_A=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage ( $I_B=0$ )	$V_{CEO}$	-40	V
Collector-Base Voltage ( $I_E=0$ )	$V_{CBO}$	-60	V
Emitter-Base Voltage ( $I_C=0$ )	$V_{EBO}$	-5	V
Collector Current-Continuous	$I_C$	0.6	A
Collector Power Dissipation	$P_{TOT}$	0.4	W
Junction Temperature	$T_J$	-55 to +125	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}\text{C}$

**Electrical Characteristics** ( $T_A=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10\mu\text{A}$ , $I_E=0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}$ , $I_E=0$	-60	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}$ , $I_C=0$	-5	-	-	V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-10\text{V}$ , $I_E=0$	-	-	-100	nA
DC Current Gain	$H_{FE}$	$V_{CE}=-10\text{V}$ , $I_C=10\text{mA}$	50	-	240	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}$ , $I_B=10\text{mA}$	-	-	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-100\text{mA}$ , $I_B=10\text{mA}$	-	-	-1.0	V
Transition Frequency	$F_T$	$I_C=-10\text{mA}$ , $V_{CE}=50\text{V}$ , $F=100\text{MHz}$	100	-	300	MHz

**Package Outline Dimensions (TO-18)**



**Pin configuration:**

- 1- Emitter
- 2- Base
- 3- Collector

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.10 TYP		0.210 TYP	
$\phi \alpha$	2.54 TYP		0.100 TYP	
$\Phi b_1$	-	1.010	-	0.040
$\Phi b_2$	0.407	0.508	0.016	0.020
$\phi D$	5.310	5.840	0.209	0.230
$\Phi D_1$	4.530	4.950	0.178	0.195
J	0.920	1.160	0.036	0.046
K	0.510	1.210	0.020	0.048
L	12.50	25.00	0.492	0.984
L1	-	1.270	-	0.050